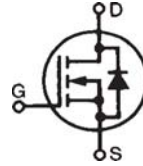


# High Voltage Power MOSFET

**IXTA1N200P3HV**  
**IXTH1N200P3HV**  
**IXTH1N200P3**

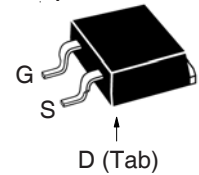
$V_{DSS} = 2000V$   
 $I_{D25} = 1.0A$   
 $R_{DS(on)} \leq 40\Omega$

N-Channel Enhancement Mode

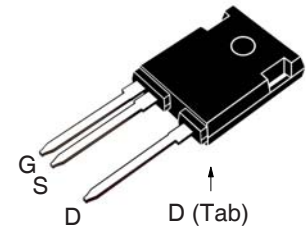


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	2000	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	2000	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	1.0	A
$I_{D110}$	$T_C = 110^\circ C$	0.6	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	3.0	A
$P_D$	$T_C = 25^\circ C$	125	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting Force (TO-263HV)	10..65 / 22..14.6	N/lb
$M_d$	Mounting Torque (TO-247/HV)	1.13/10	Nm/lb.in
<b>Weight</b>	TO-263HV	2.5	g
	TO-247/HV	6.0	g

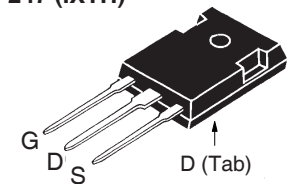
TO-263HV (IXTA)



TO-247HV (IXTH)



TO-247 (IXTH)



G = Gate      D = Drain  
S = Source    Tab = Drain

## Features

- High Blocking Voltage
- High Voltage Packages

## Advantages

- Easy to Mount
- Space Savings
- High Power Density

## Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	2000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.0		4.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			5 $\mu A$
				100 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5A$ , Note 1			40 $\Omega$

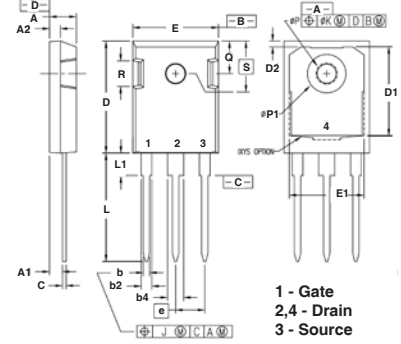
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 50\text{V}$ , $I_D = 0.5\text{A}$ , Note 1	0.4	0.7	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		646	pF
$C_{oss}$			50	pF
$C_{rss}$			17	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 1\text{kV}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 5\Omega$ (External)		16	ns
$t_r$			26	ns
$t_{d(off)}$			37	ns
$t_f$			80	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 1\text{kV}$ , $I_D = 0.5 \cdot I_{D25}$		23.5	nC
$Q_{gs}$			3.1	nC
$Q_{gd}$			13.3	nC
$R_{thJC}$	TO-247			1.0 $^\circ\text{C/W}$
$R_{thCS}$			0.21	$^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			1 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			4 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 1\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$		2.3	$\mu\text{s}$

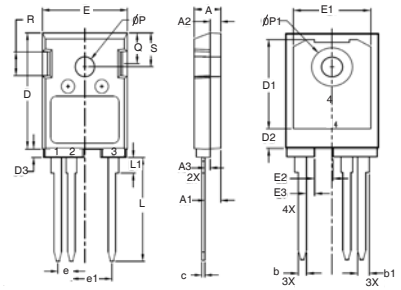
Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**TO-247 Outline**



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC 0.215 BSC			
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Ø P1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC 0.242 BSC			

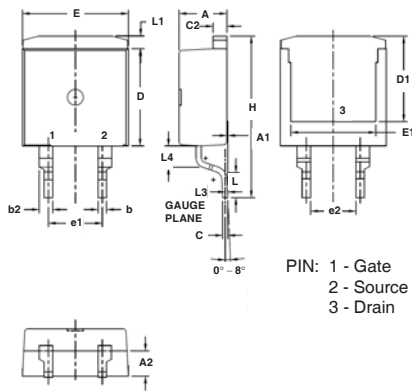
**TO-247HV Outline**



PINS:  
1 - Gate 2 - Source  
3, 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100 BSC 2.54 BSC			
e1	.300 BSC 7.62 BSC			
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
Ø P	.138	.142	3.50	3.60
Ø P1	.272	.280	6.90	7.10
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30
S	.240	.248	6.10	6.30

**TO-263HV Outline**



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200 BSC 5.08 BSC			
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010 BSC 0.254 BSC			
(L4)	.071	.087	1.80	2.20

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

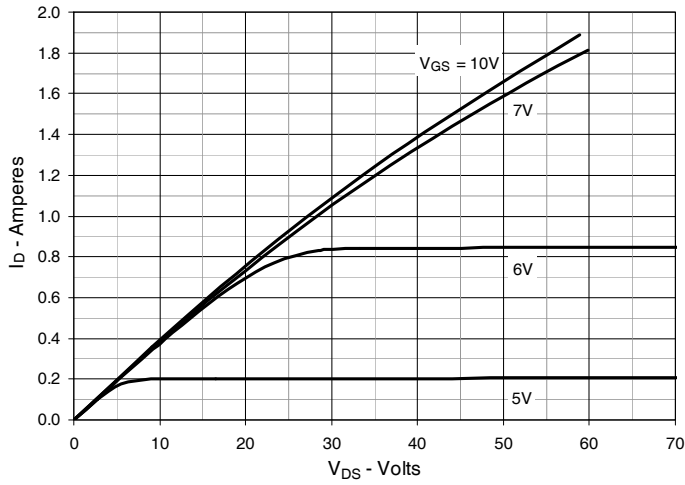


Fig. 2. Output Characteristics @  $T_J = 125^\circ\text{C}$

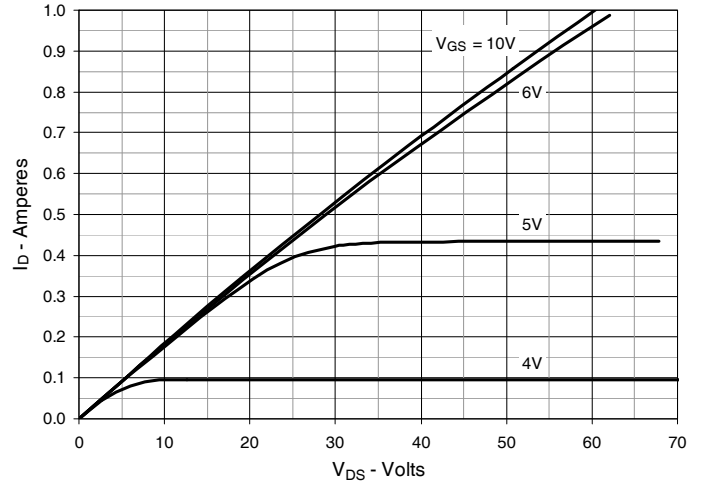


Fig. 3.  $R_{DS(on)}$  Normalized to  $I_D = 0.5\text{A}$  Value vs. Junction Temperature

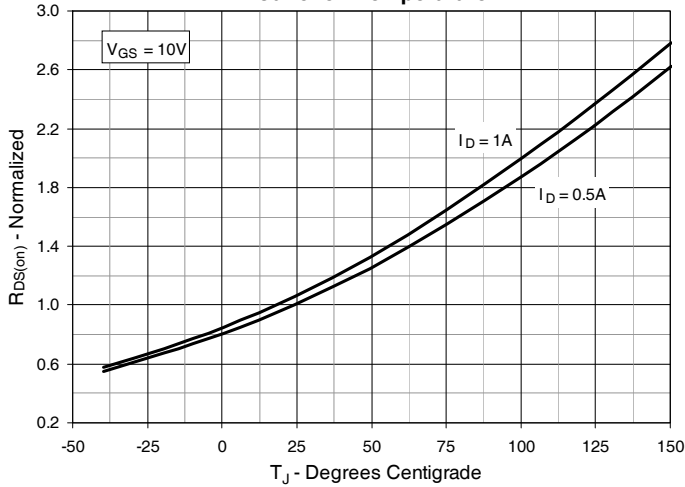


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 0.5\text{A}$  Value vs. Drain Current

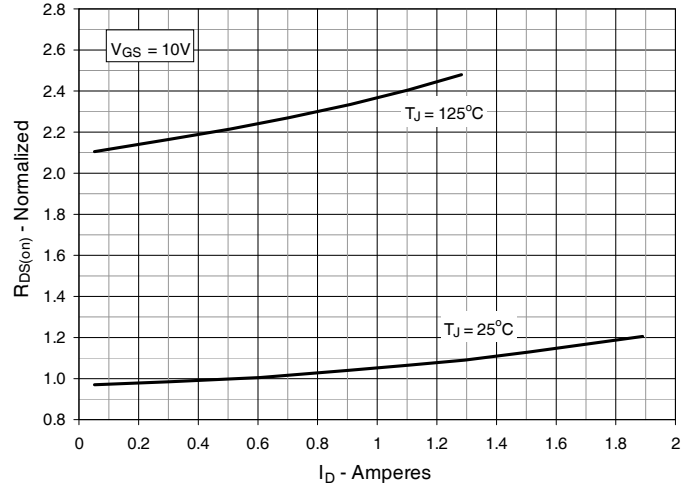


Fig. 5. Maximum Drain Current vs. Case Temperature

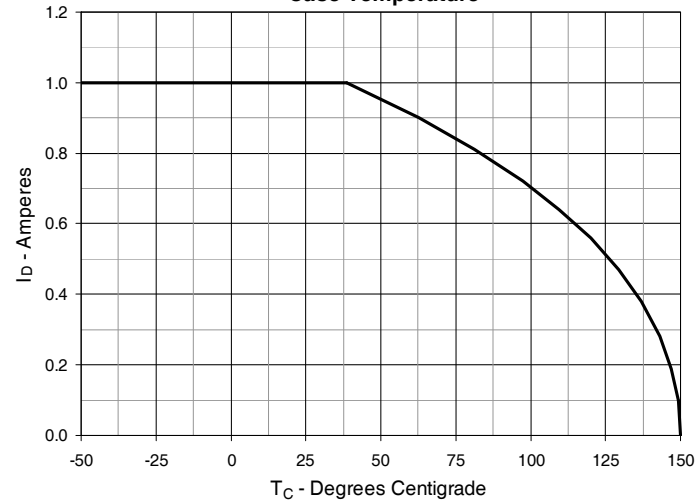


Fig. 6. Input Admittance

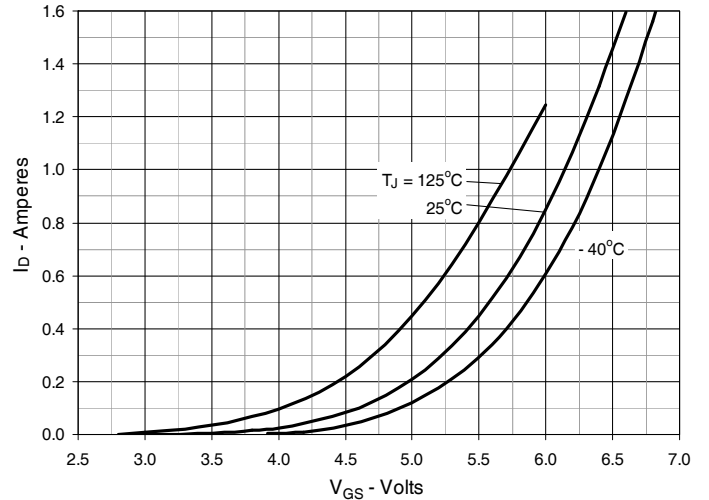


Fig. 7. Transconductance

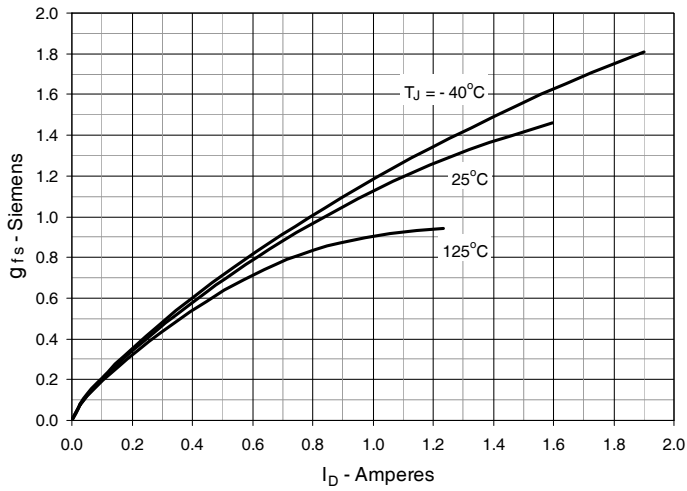


Fig. 8. Forward Voltage Drop of Intrinsic Diode

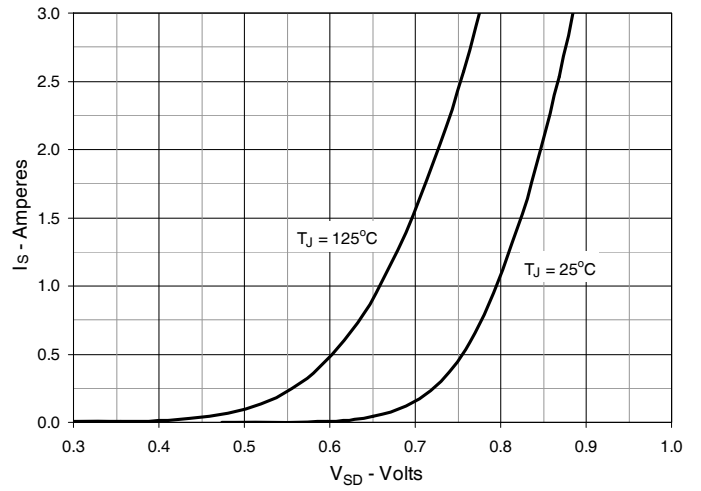


Fig. 9. Gate Charge

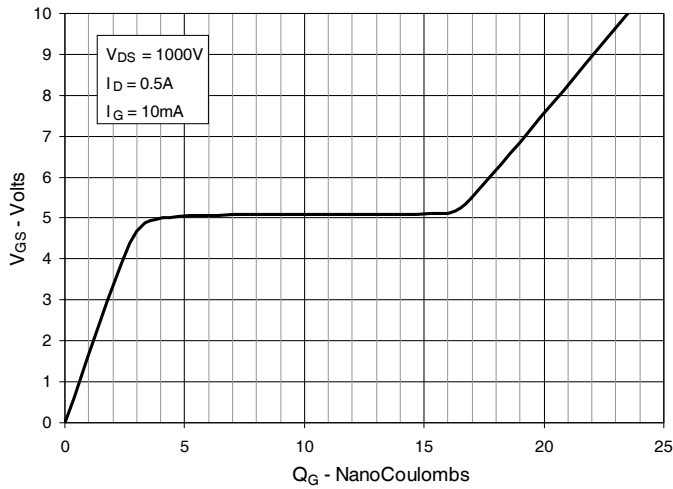


Fig. 10. Capacitance

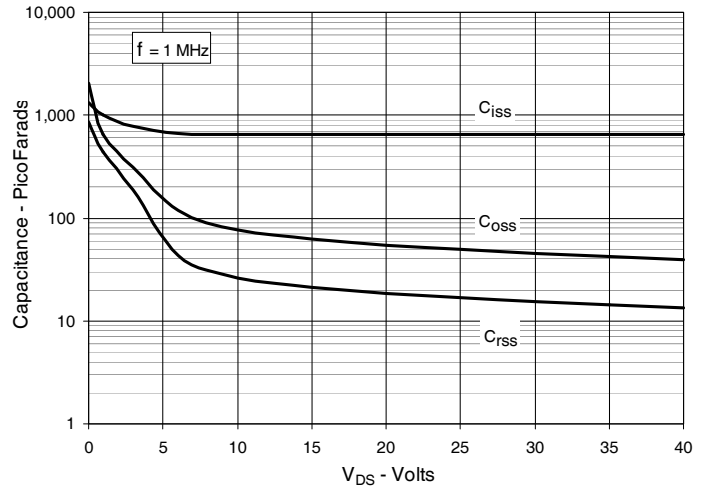


Fig. 11. Maximum Transient Thermal Impedance

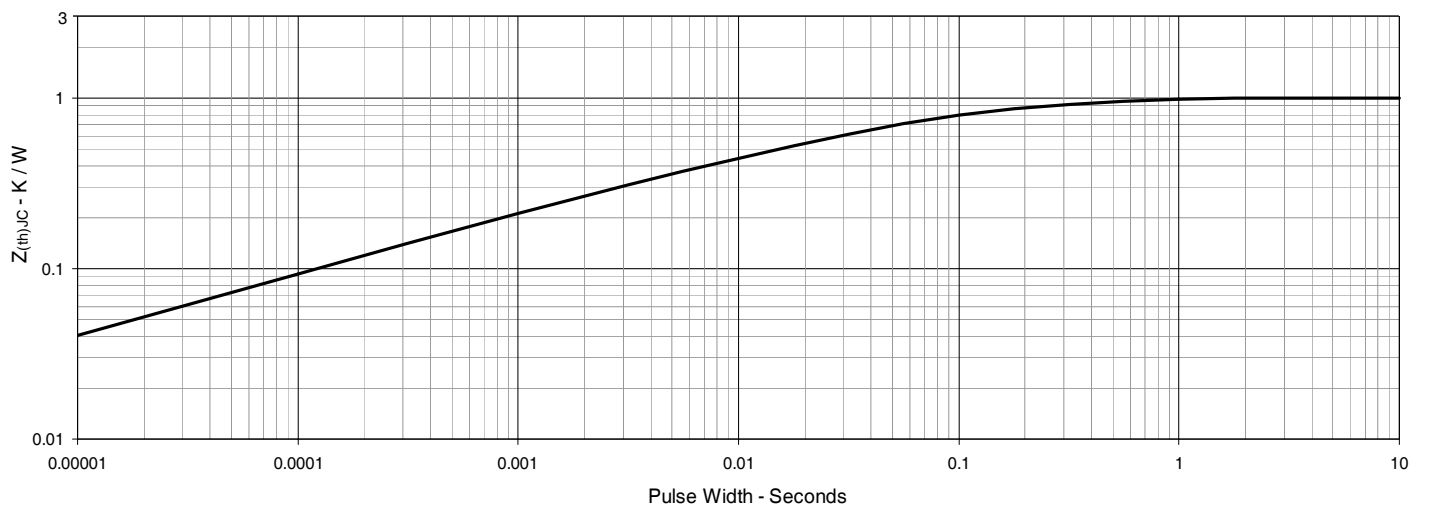


Fig. 12. Forward-Bias Safe Operating Area  
@  $T_C = 25^\circ\text{C}$

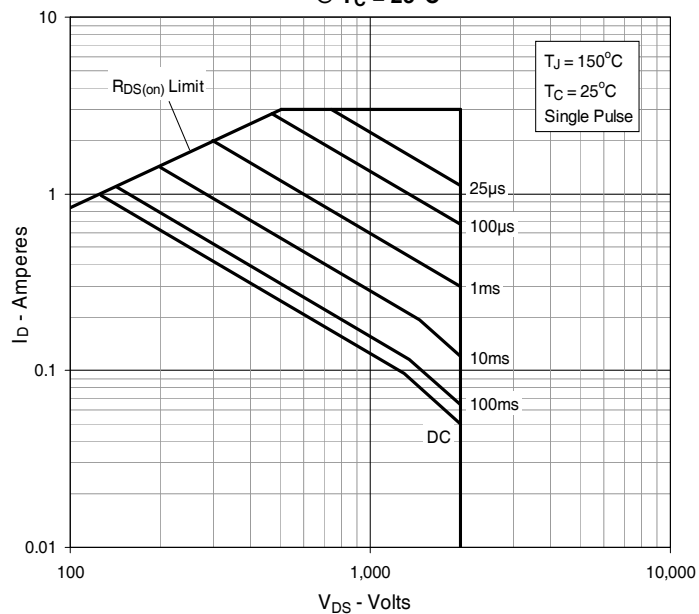
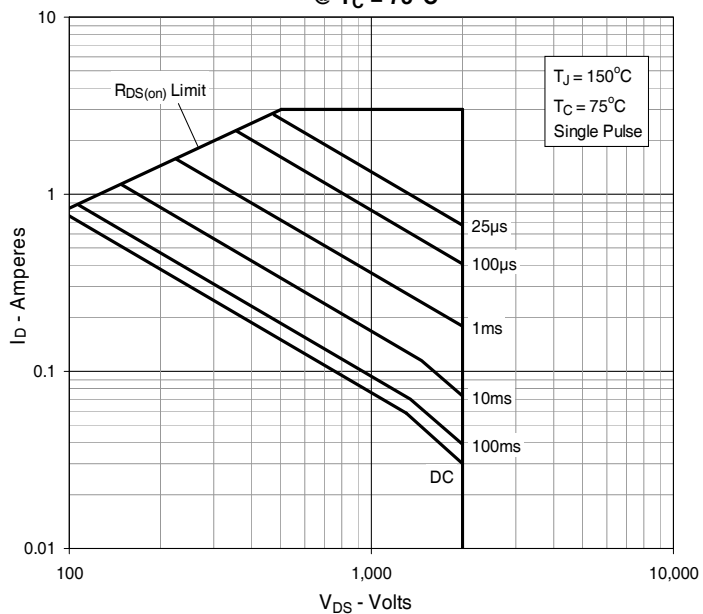


Fig. 13. Forward-Bias Safe Operating Area  
@  $T_C = 75^\circ\text{C}$





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